SUPPORTING INFORMATION

Thermoelectric Characteristics of Sb_2Te_3 Thin Films Formed via Surfactant-Assisted Electrodeposition

In-Joon Yoo[a,b], Youngsup Song[a], Dong Chan Lim[a], Nosang V. Myung[c], Kyu Hyoung Lee[d], Minju Oh[e], Dongyun Lee[e], Yang Do Kim[b], Seil Kim[f], Yong-Ho Choa[f], Joo Yul Lee[a], Kyu Hwan Lee[a], and Jae-Hong Lim[a*]

[a]*Electrochemistry Department , Korea Institute of Materials Science, Changwon 641-010, Korea*

[b]*School of Materials Science and Engineering, Pusan National University, Busan 609-735, Korea*

[c]*Department of Chemical and Environmental Engineering, University of California-Riverside, Riverside, CA 92521*

[d]*Advanced Materials Research Center, Samsung Advanced Institute of Technology, Samsung Electronics, Yongin 446-712, Korea*

[e] *Department of NanoFusion Technology, Pusan National University, Busan 609-735, Korea*

[f]*Department of Bionano Technology, Hanyang University, Ansan 426-791, Korea*

[*] Author to whom all correspondence should be addressed;

E- mail: lim@kims.re.kr

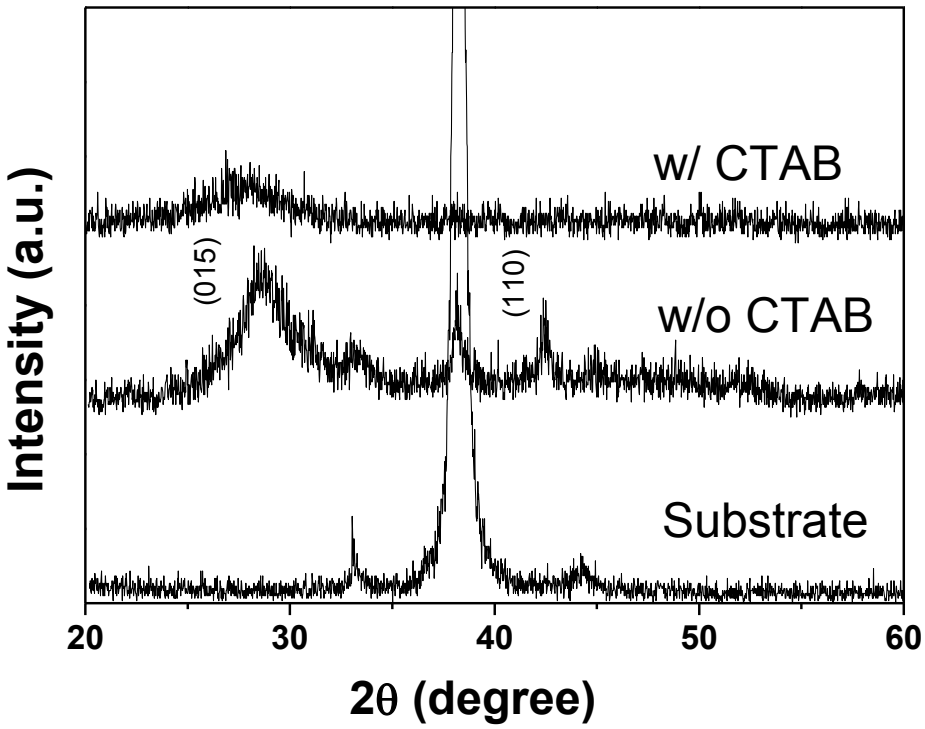
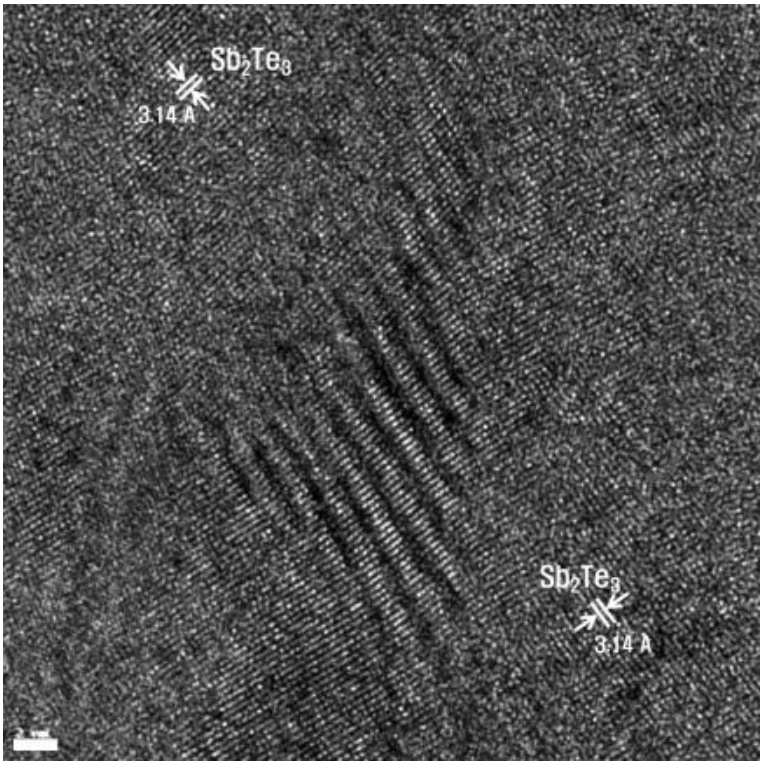
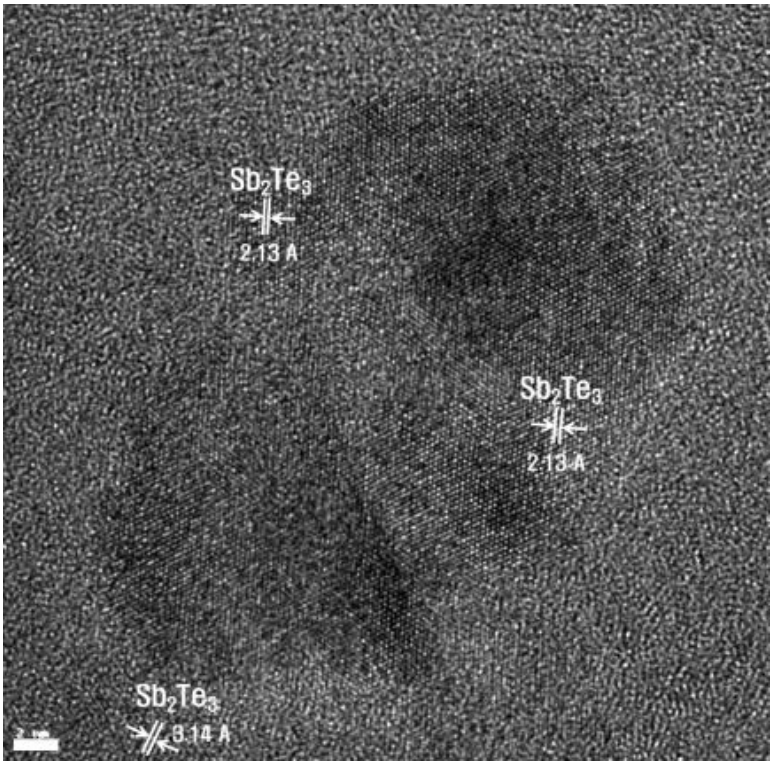


Figure S1. XRD patterns of the Sb_2Te_3 films formed with and without CTAB.



(a)



(b)

Figure S2. TEM images (scale bar = 2 nm) of the Sb_2Te_3 films formed without CTAB: (a) before and (b) after annealing at 200 °C.